

2DB1132P/Q/R

32V PNP POWER SWITCHING TRANSISTOR IN SOT89

Features

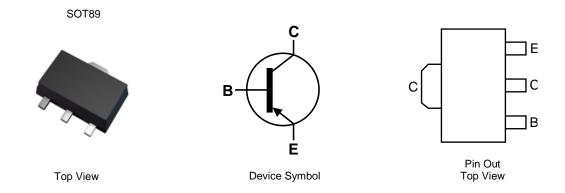
- BV_{CEO} > -32V
- I_c = -1A High Continuous Collector Current
- Complementary NPN Type: 2DD1664
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.055 grams (Approximate)



Ordering Information (Note 4)

Part Number	Status	Marking Code	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
2DB1132P-13	Obsolete	P13P	13	12	2,500
2DB1132Q-13	Obsolete	P13Q	13	12	2,500
2DB1132R-13	Active	P13R	13	12	2,500
2DB1132R-13R	Active	P13R	13	12	4,000

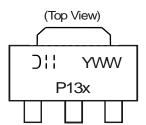
Notes:

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} \bigcirc 11 = \text{Manufacturer's Marking} \\ \text{P13x} = \text{Product Type Marking Code:} \\ \text{Where} \quad \begin{array}{l} \text{P13P} = 2\text{DB1132P} \\ \text{P13Q} = 2\text{DB1132Q} \\ \text{P13R} = 2\text{DB1132R} \\ \text{YWW} = \text{Date Code Marking} \\ \text{Y} = \text{Last Digit of Year (ex: 1 = 2021)} \\ \text{WW} = \text{Week Code (01 to 52)} \end{array}$



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	-40	V
Collector-Emitter Voltage	VCEO	-32	V
Emitter-Base Voltage	VEBO	-5	V
Continuous Collector Current	lc	-1	А
Peak Pulse Current	I _{CM}	-2	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1		
Power Dissipation	(Note 6)	PD	1.5	W	
	(Note 7)		2		
	(Note 5)		125		
Thermal Resistance, Junction to Ambient Air	(Note 6)	Reja	83	°C/W	
	(Note 7)		60		
Thermal Resistance, Junction to Case	(Note 5)	Rejc	18	°C/W	
Thermal Resistance, Junction to Lead	(Note 8)	Rejl	22	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

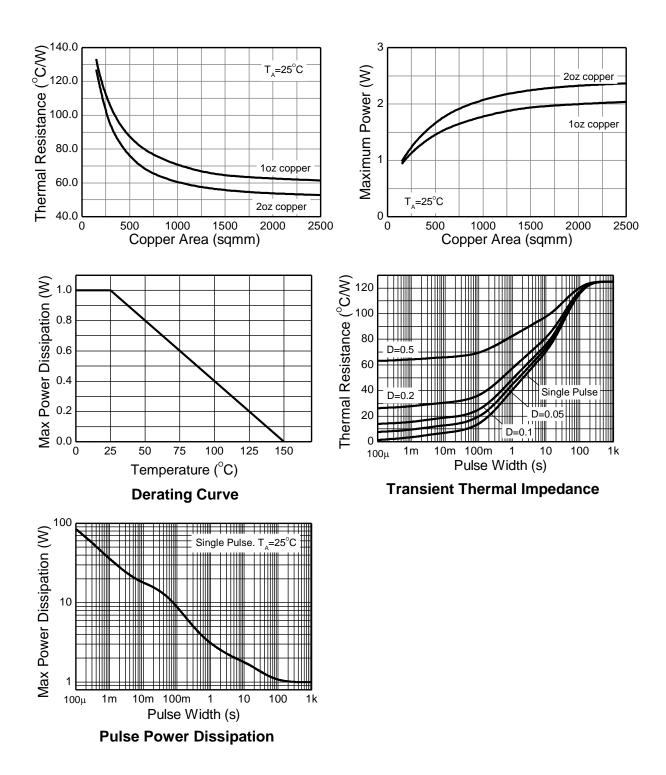
6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.

7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.

Thermal resistance from junction to solder-point (on the exposed collector pad).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



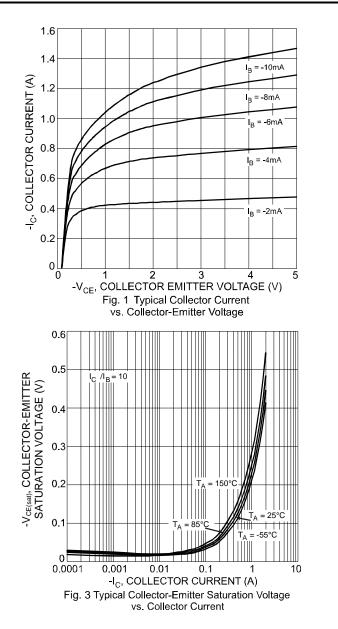


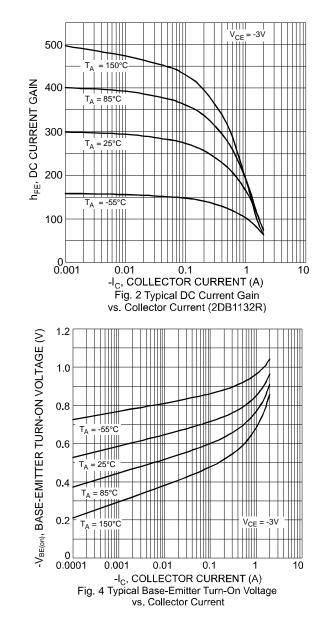
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		ВУсво	-40	—	-	V	Ic = -50μA
Collector-Emitter Breakdown Voltage (Note 10)		BVCEO	-32	_	—	V	Ic = -1mA
Emitter-Base Breakdown Voltage		BVEBO	-5	—	—	V	I _E = -50μA
Collector Cut-Off Current		Ісво	_	_	-0.5	μA	V _{CB} = -20V
Emitter Cut-Off Current		I _{EBO}	—	_	-0.5	μA	$V_{EB} = -4V$
Static Forward Current Transfer Ratio (Note 10)	2DB1132P 2DB1132Q 2DB1132R	hfe	82 120 180	_	180 270 390	—	Ic = -100mA, Vce = -3V
Collector-Emitter Saturation Voltage (Note 10)		V _{CE(sat)}	_	-125	-500	mV	I _C =-500mA, I _B = -50mA
Transition Frequency		f⊤	-	190	_	MHz	$I_E = -50$ mA, $V_{CE} = -5V$, f = 30MHz
Output Capacitance		Cobo	_	12	30	pF	$I_E = 0A$, $V_{CB} = -10V$, $f = 1MHz$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

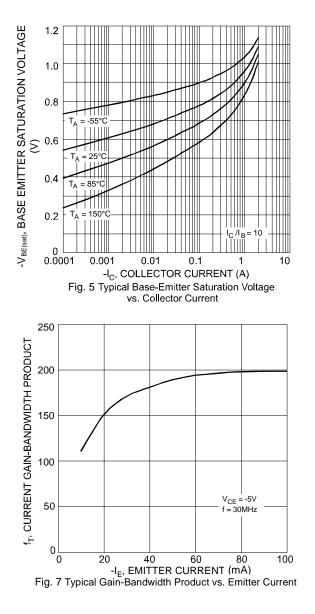
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

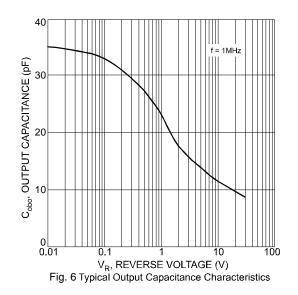






Typical Electrical Characteristics (continued) (@TA = +25°C, unless otherwise specified.)

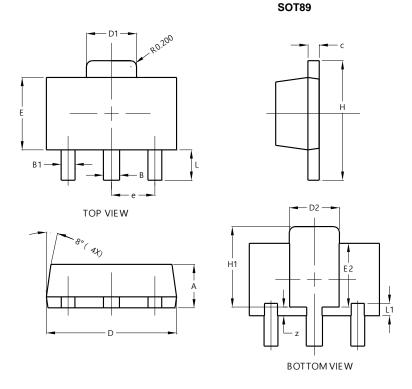






Package Outline Dimensions

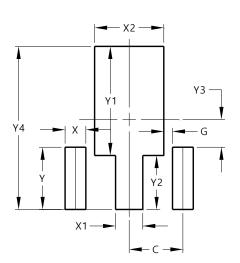
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT89							
Dim	Min	Max	Тур				
Α	1.40	1.60	1.50				
в	0.50	0.62	0.56				
B1	0.42	0.54	0.48				
c	0.35	0.43	0.38				
D	4.40	4.60	4.50				
D1	1.62	1.83	1.733				
D2	1.61	1.81	1.71				
Е	2.40	2.60	2.50				
E2	2.05	2.35	2.20				
е	-	-	1.50				
Н	3.95	4.25	4.10				
H1	2.63	2.93	2.78				
L	0.90	1.20	1.05				
L1	0.327	0.527	0.427				
z	0.20	0.40	0.30				
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	1.500		
-			
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Y	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		

SOT89



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